

# LP8551 High-Efficiency LED Backlight Driver for Notebooks

Check for Samples: LP8551

## **FEATURES**

- High-Voltage DC/DC Boost Converter with Integrated FET with Four Switching Frequency Options: 156/312/625/1250 kHz
- 2.7V 22V Input Voltage Range to Support 1x...5x Cell Li-Ion Batteries
- Programmable PWM Resolution 8 to 13 Bits
- I<sup>2</sup>C and PWM Brightness Control
- PWM Output Frequency and LED Current Set Through Resistors
- 4 LED Outputs with LED Fault (short/open) Detection
- Low Input Voltage, Over-Temperature, Over-Current Detection and Shutdown
- Minimum Number of External Components
- DSBGA-25 Package, 2.466 x 2.466 x 0.6 mm

#### **APPLICATIONS**

- Notebook and Netbook LCD Display LED Backlight
- LED Lighting

### DESCRIPTION

The LP8551 is a white LED driver with integrated boost converter. It has four adjustable current sinks which can be controlled by PWM input or with I<sup>2</sup>C-compatible serial interface.

The boost converter has adaptive output voltage control based on the LED driver voltages. This feature minimizes the power consumption by adjusting the voltage to lowest sufficient level in all conditions.

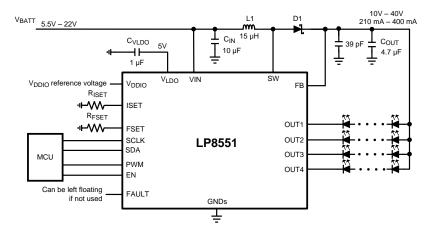
LED outputs have 8-bit current resolution and up to 13-bit PWM resolution to achieve smooth and precise brightness control. Proprietary Phase Shift PWM control is used for LED outputs to reduce peak current from the boost converter, thus making the boost capacitors smaller. The Phase Shifting scheme also eliminates audible noise.

Internal EEPROM is used for storing the configuration data. This makes it possible to have minimum external component count and make the solution very small.

LP8551 has safety features which make it possible to detect LED outputs with open or short fault. As well low input voltage and boost over-current conditions are monitored and chip is turned off in case of these events. Thermal de-rating function prevents overheating of the device by reducing backlight brightness when set temperature has been reached.

LP8551 is available in TI's DSBGA-25 package.

## **Typical Application**

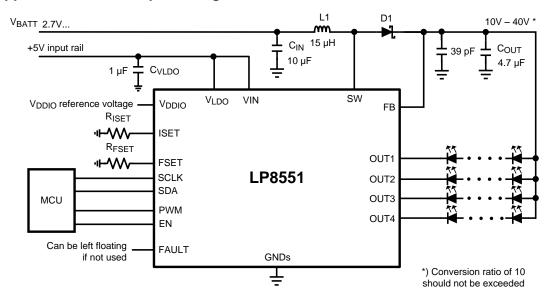


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# **Typical Application for Low Input Voltage**



Separate 5V rail to  $V_{LDO}$  can be also used to improve efficiency for applications with higher battery voltage. No power sequencing requirements between  $V_{IN}/V_{LDO}$  and  $V_{BATT}$ 

## **Connection Diagrams**

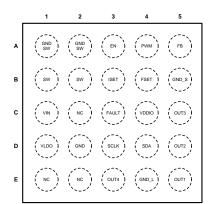


Figure 1. DSBGA-25 Package Top View Package Number YZR002511A

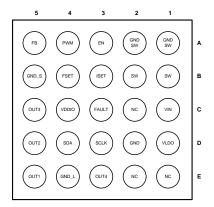


Figure 2. DSBGA-25 Package Bottom View Package Number YZR002511A

## Package Mark

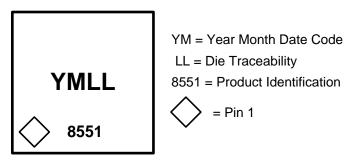


Figure 3. Package Mark - Top View



## **Pin Descriptions**

Pin#	Name	Type <sup>(1)</sup>	Description
A1	GND_SW	G	Boost switch ground
A2	GND_SW	G	Boost switch ground
А3	EN	1	Enable input pin
A4	PWM	А	PWM dimming input. This pin must be connected to GND if not used.
A5	FB	А	Boost feedback input
B1	SW	А	Boost switch
B2	SW	А	Boost switch
В3	ISET	А	Set resistor for LED current. This pin can be left floating if not used.
B4	FSET	А	PWM frequency set resistor. This pin can be left floating if not used.
B5	GND_S	G	Signal ground
C1	VIN	Р	Input power supply up to 22V. If 2.7V ≤ VBATT < 5.5V (typ. app. (2)) then external 5V rail must be used for VLDO and VIN.
C2	NC	-	Not connected
C3	FAULT	OD	Fault indication output. If not used, can be left floating.
C4	VDDIO	Р	Digital IO reference voltage (1.65V5V) for I <sup>2</sup> C interface. If brightness is controlled with PWM input pin then this pin can be connected to GND.
C5	OUT3	Α	Current sink output
D1	VLDO	Р	LDO output voltage. External 5V rail can be connected to this pin in low voltage application.
D2	GND	G	Ground
D3	SCLK	I	Serial clock. This pin must be connected to GND if not used.
D4	SDA	I/O	Serial data. This pin must be connected to GND if not used.
D5	OUT2	Α	Current sink output
E1	NC	-	Not connected
E2	NC	-	Not connected
E3	OUT4	А	Current sink output
E4	GND_L	G	LED ground
E5	OUT1	А	Current sink output

(1) A: Analog Pin, G: Ground Pin, P: Power Pin, I: Input Pin, I/O: Input/Output Pin, O: Output Pin, OD: Open Drain Pin



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.



# **Absolute Maximum Ratings**(1)(2)

V <sub>IN</sub>		-0.3V to +24.0V		
$V_{LDO}$		-0.3V to +6.0V		
Voltage on Logic Pins (PWM, EN, SCLK, SD	-0.3V to +6.0V			
Voltage on Logic Pin (FAULT)		-0.3V to VDDIO + 0.3V		
Voltage on Analog Pins (VDDIO, ISET, FSET	-)	-0.3V to +6.0V		
V (OUT1OUT4, SW, FB)		-0.3V to +44.0V		
Continuous Power Dissipation (3)	Internally Limited			
Junction Temperature (T <sub>J-MAX</sub> )		125 °C		
Storage Temperature Range		-65 °C to +150 °C		
Maximum Lead Temperature (Soldering)		See <sup>(4)</sup>		
ESD Rating <sup>(5)</sup>	Human Body Model	2 kV		
	Machine Model	200V		
	Charged Device Model	1 kV		

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the component may occur. Operating Ratings are conditions under which operation of the device is specified. Operating Ratings do not imply specified performance limits. For specified performance limits and associated test conditions, see the Electrical Characteristics tables.
- (2) All voltages are with respect to the potential at the GND pins.
- (3) Internal thermal shutdown circuitry protects the device from permanent damage. Thermal shutdown engages at T<sub>J</sub> = 150 °C (typ.) and disengages at T<sub>J</sub> = 130 °C (typ.).
- (4) For detailed soldering specifications and information, please refer to Tl's AN-1112 (SNVA009): DSBGA Wafer Level Chip Scale Package.
- (5) Human Body Model, applicable standard JESD22-A114C. Machine Model, applicable standard JESD22- A115-A. Charged Device Model, applicable standard JESD22A-C101.

# Operating Ratings<sup>(1)(2)</sup>

Input Voltage Range (V <sub>IN</sub> ) Typical Application	5.5V to 22.0V
Input Voltage Range (V <sub>IN</sub> + V <sub>LDO</sub> ) Typical Application for Low Input Voltage	4.5V to 5.5V
$V_{DDIO}$	1.65V to 5V
V(OUT1OUT4, SW, FB)	0V to 40V
Junction Temperature (T <sub>J</sub> ) Range	-30 °C to +125 °C
Ambient Temperature (T <sub>A</sub> ) Range <sup>(3)</sup>	-30 °C to +85 °C

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the component may occur. Operating Ratings are conditions under which operation of the device is specified. Operating Ratings do not imply specified performance limits. For specified performance limits and associated test conditions, see the Electrical Characteristics tables.
- (2) All voltages are with respect to the potential at the GND pins.
- (3) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature (T<sub>A-MAX</sub>) is dependent on the maximum operating junction temperature (T<sub>J-MAX-OP</sub> = 125 °C), the maximum power dissipation of the device in the application (P<sub>D-MAX</sub>), and the junction-to ambient thermal resistance of the part/package in the application (θ<sub>JA</sub>), as given by the following equation: T<sub>A-MAX</sub> = T<sub>J-MAX-OP</sub> (θ<sub>JA</sub> × P<sub>D-MAX</sub>).

## **Thermal Properties**

Junction-to-Ambient Thermal Resistance (θ <sub>JA</sub> ), YZR002511A Package <sup>(1)</sup>	40 - 73 °C/W
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 Junction-to-ambient thermal resistance is highly application and board-layout dependent. In applications where high maximum power dissipation exists, special care must be paid to thermal dissipation issues in board design.



# Electrical Characteristics (1)(2)

Limits in standard typeface are for  $T_A$  = 25 °C. Limits in **boldface** type apply over the full operating junction temperature range (-30 °C ≤  $T_A$  ≤ +85 °C). Unless otherwise specified:  $V_{IN}$  = 12.0V,  $V_{DDIO}$  = 2.8V,  $C_{VLDO}$  = 1  $\mu$ F, L1 = 15  $\mu$ H,  $C_{IN}$  = 10  $\mu$ F,  $C_{OUT}$  = 10  $\mu$ F.  $R_{ISET}$  = 16  $k\Omega^{(3)}$ 

Symbol	Parameter	Condition	Min	Тур	Max	Units	
	Standby Supply Current	Internal LDO disabled EN=L and PWM=L			1	μΑ	
I <sub>IN</sub>	Normal Mode Supply Current	LDO enabled, boost enabled, no current going through LED outputs 5 MHz PLL Clock		3.0			
		10 MHz PLL Clock		3.7		mA	
		20 MHz PLL Clock		4.7			
		40 MHz PLL Clock		6.7			
f <sub>OSC</sub>	Internal Oscillator Frequency Accuracy		-4 <b>-7</b>		+4 <b>+7</b>	%	
$V_{LDO}$	Internal LDO Voltage		4.5	5.0	5.5	V	
I <sub>LDO</sub>	Internal LDO External Loading				5.0	mA	

- (1) All voltages are with respect to the potential at the GND pins.
- (2) Min and Max limits are specified by design, test, or statistical analysis. Typical numbers are not specified, but do represent the most likely norm.
- (3) Low-ESR Surface-Mount Ceramic Capacitors (MLCCs) used in setting electrical characteristics.

#### **Boost Converter Electrical Characteristics**

Symbol	Parameter	Condition	Min	Тур	Max	Units
RDS <sub>ON</sub>	Switch ON Resistance	I <sub>SW</sub> = 0.5A		0.12		Ω
V <sub>MAX</sub>	Boost Maximum Output Voltage			40		V
		9.0V ≤ V <sub>BATT</sub> , V <sub>OUT</sub> = 35V		450		
$I_{LOAD}$	Maximum Continuous Load Current	6.0V ≤ V <sub>BATT</sub> , V <sub>OUT</sub> = 35V		300		mA
	Odificial	$3.0V \le V_{BATT}, V_{OUT} = 25V$		180		
V <sub>OUT</sub> /V <sub>IN</sub>	Conversion Ratio	f <sub>SW</sub> = 1.25 MHz			10	
f <sub>SW</sub>	Switching Frequency	BOOST_FREQ = 00 BOOST_FREQ = 01 BOOST_FREQ = 10 BOOST_FREQ = 11		156 312 625 1250		kHz
V <sub>OV</sub>	Over-voltage Protection Voltage			V <sub>BOOST</sub> + 1.6V		V
t <sub>PULSE</sub>	Switch Pulse Minimum Width	no load		50		ns
t <sub>STARTUP</sub>	Startup Time	See <sup>(1)</sup>		6		ms
I <sub>MAX</sub>	SW Pin Current Limit IMAX_SEL = 0 IMAX_SEL = 1			1.4 2.5		А

(1) Start-up time is measured from the moment boost is activated until the  $V_{OUT}$  crosses 90% of its target value.



## **LED Driver Electrical Characteristics**

Symbol	Parameter	Condition	Min	Тур	Max	Units	
I <sub>LEAKAGE</sub>	Leakage Current	Outputs OUT1OUT4, V <sub>OUT</sub> = 40V		0.1	1	μΑ	
	Maximum Source Current	EN_I_RES = 0, CURRENT[7:0] = FFh		30			
I <sub>MAX</sub>	OUT1OUT4	EN_I_RES = 1, CURRENT[7:0] = FFh		50		mA	
I <sub>OUT</sub>	Output Current Accuracy <sup>(1)</sup>	Output current set to 23 mA, EN_I_RES = 1	-3 <b>-4</b>		+3 +4	%	
I <sub>MATCH</sub>	Matching <sup>(1)</sup>	Output current set to 23 mA, EN_I_RES = 1		0.5		%	
	PWM Output Resolution <sup>(2)</sup>	$f_{LED} = 5 \text{ kHz}, f_{PLL} = 5 \text{ MHz}$		10		bits	
		$f_{LED} = 10 \text{ kHz}, f_{PLL} = 5 \text{ MHz}$		9			
DVVVV		$f_{LED} = 20 \text{ kHz}, f_{PLL} = 5 \text{ MHz}$		8			
PWM <sub>RES</sub>		$f_{LED} = 5 \text{ kHz}, f_{PLL} = 40 \text{ MHz}$		13		Dits	
		$f_{LED} = 10 \text{ kHz}, f_{PLL} = 40 \text{ MHz}$		12			
		$f_{LED} = 20 \text{ kHz}, f_{PLL} = 40 \text{ MHz}$		11			
	LED Switching Frequency <sup>(2)</sup>	PWM_FREQ[4:0] = 00000b PLL clock 5 MHz		600		11-	
f <sub>LED</sub>		PWM_FREQ[4:0] = 11111b PLL clock 5 MHz		19.2k		Hz	
V	Caturation Valtage (3)	Output current set to 20 mA		105	220	m)/	
V <sub>SAT</sub>	Saturation Voltage (3)	Output current set to 30 mA		160	290	mV	

- Output Current Accuracy is the difference between the actual value of the output current and programmed value of this current. Matching is the maximum difference from the average. For the constant current sinks on the part (OUT1 to OUT4), the following are determined: the maximum output current (MAX), the minimum output current (MIN), and the average output current of all outputs (AVG). Two matching numbers are calculated: (MAX-AVG)/AVG and (AVG-MIN/AVG). The largest number of the two (worst case) is considered the matching figure. The typical specification provided is the most likely norm of the matching figure for all parts. Note that some manufacturers have different definitions in use.
- PWM output resolution and frequency depend on the PLL settings. Please see section PWM Frequency Setting for full description Saturation voltage is defined as the voltage when the LED current has dropped 10% from the value measured at 1V.

## **PWM Interface Characteristics**

Symbol	Parameter	Condition	Min	Тур	Max	Units
f <sub>PWM</sub>	PWM Frequency Range		0.1		25	kHz
t <sub>MIN_ON</sub>	Minimum Pulse ON time			1		
t <sub>MIN_OFF</sub>	Minimum Pulse OFF time			1		μs
t <sub>STARTUP</sub>	Turn on delay from standby to backlight on	PWM input active, EN pin rise from low to high		6		ms
T <sub>STBY</sub>	Turn Off Delay	PWM input low time for turn off, slope disabled		50		ms
PWM <sub>RES</sub>	PWM Input Resolution	$ f_{IN} < 9.0 \text{ kHz} \\  f_{IN} < 4.5 \text{ kHz} \\  f_{IN} < 2.2 \text{ kHz} \\  f_{IN} < 1.1 \text{ kHz} $		10 11 12 13		bits

## **Under-Voltage Protection**

Symbol	Parameter	Condition	Min	Тур	Max	Units
V <sub>UVLO</sub> V <sub>IN</sub> UV		UVLO[1:0] = 00		Disabled		
		UVLO[1:0] = 01, falling	2.55	2.70	2.94	
		UVLO[1:0] = 01, rising	2.62	2.76	3.00	
	V <sub>IN</sub> UVLO Threshold Voltage	UVLO[1:0] = 10, falling	5.11	5.40	5.68	V
		UVLO[1:0] = 10, rising	5.38	5.70	5.98	
		UVLO[1:0] = 11, falling	7.75	8.10	8.45	
		UVLO[1:0] = 11, rising	8.36	8.73	9.20	



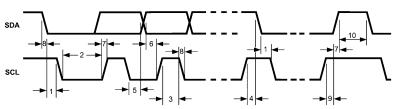
# **Logic Interface Characteristics**

Symbol	Parameter	Condition	Min	Тур	Max	Units
Logic In	put EN	•				
V <sub>IL</sub>	Input Low Level				0.4	V
V <sub>IH</sub>	Input High Level		1.2			V
I	Input Current		-1.0		1.0	μΑ
Logic In	put PWM		·			
V <sub>IL</sub>	Input Low Level				0.4	V
V <sub>IH</sub>	Input High Level		2.2			V
I <sub>I</sub>	Input Current		-1.0		1.0	μΑ
Logic In	puts SCL, SDA	·				
V <sub>IL</sub>	Input Low Level				0.2xV <sub>DDIO</sub>	V
V <sub>IH</sub>	Input High Level		0.8xV <sub>DDIO</sub>			V
l <sub>l</sub>	Input Current		-1.0		1.0	μΑ
Logic Ou	utputs SDA, FAULT					
V <sub>OL</sub>	Output Low Level	I <sub>OUT</sub> = 3 mA (pull-up current)		0.3	0.5	V
IL	Output Leakage Current	V <sub>OUT</sub> = 2.8V	-1.0		1.0	μA

# I<sup>2</sup>C SERIAL BUS TIMING PARAMETERS (SDA, SCLK)<sup>(1)</sup>

0	B 1	Lin	nit	11-16-
Symbol	Parameter	Min	Max	Units
f <sub>SCLK</sub>	Clock Frequency		400	kHz
1	Hold Time (repeated) START Condition	0.6		μs
2	Clock Low Time	1.3		μs
3	Clock High Time	600		ns
4	Setup Time for a Repeated START Condition	600		ns
5	Data Hold Time	50		ns
6	Data Setup Time	100		ns
7	Rise Time of SDA and SCL	20+0.1C <sub>b</sub>	300	ns
8	Fall Time of SDA and SCL	15+0.1C <sub>b</sub>	300	ns
9	Set-up Time for STOP condition	600		ns
10	Bus Free Time between a STOP and a START Condition	1.3		μs
C <sub>b</sub>	Capacitive Load Parameter for Each Bus Line Load of 1 pF corresponds to 1 ns.	10	200	ns

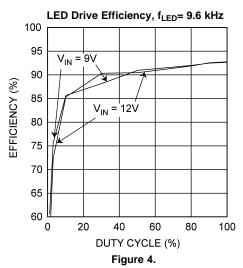
## (1) Specified by design. $V_{DDIO} = 1.65V$ to 5.5V.

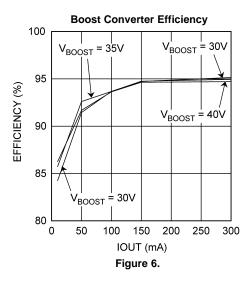


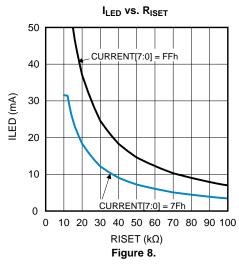


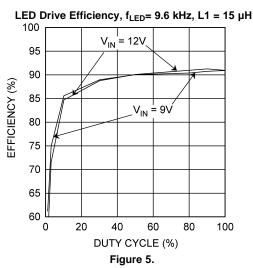
# **Typical Performance Characteristics**

Unless otherwise specified:  $V_{BATT}$ = 12.0V,  $C_{VLDO}$ = 1  $\mu$ F, L1 = 33  $\mu$ H,  $C_{IN}$ = 10  $\mu$ F,  $C_{OUT}$ = 10  $\mu$ F









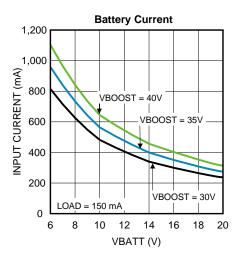


Figure 7.

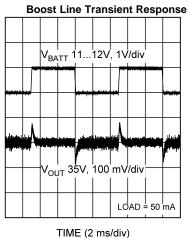
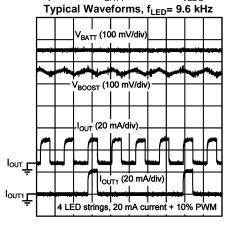


Figure 9.

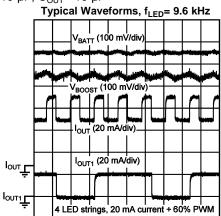


# **Typical Performance Characteristics (continued)**

Unless otherwise specified:  $V_{BATT}$ = 12.0V,  $C_{VLDO}$ = 1  $\mu$ F, L1 = 33  $\mu$ H,  $C_{IN}$ = 10  $\mu$ F,  $C_{OUT}$ = 10  $\mu$ F Typical Waveforms,  $f_{LED}$ = 9.6 kHz



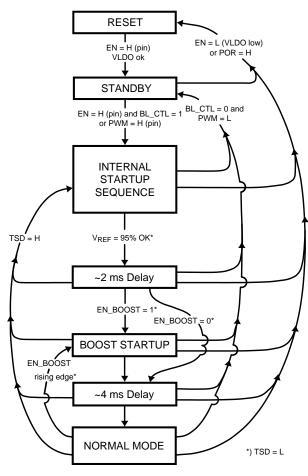
TIME (20 µs/DIV) Figure 10.



TIME (20 µs/DIV) Figure 11.



#### **MODES OF OPERATION**



- **RESET:** In the RESET mode all the internal registers are reset to the default values. Reset is entered always when VLDO voltage is low. EN pin is enable for the internal LDO. Power On Reset (POR) will activate during the chip startup or when the supply voltage VLDO fall below POR level. Once VLDO rises above POR level, POR will inactivate and the chip will continue to the STANDBY mode.
- **STANDBY:** The STANDBY mode is entered if the register bit BL\_CTL is LOW and external PWM input is not active and POR is not active. This is the low power consumption mode, when only internal 5V LDO is enabled. Registers can be written in this mode and the control bits are effective immediately after start up.
- **STARTUP:** When BL\_CTL bit is written high or PWM signal is high, the INTERNAL STARTUP SEQUENCE powers up all the needed internal blocks (VREF, Bias, Oscillator etc.). Internal EPROM and EEPROM are read in this mode. To ensure the correct oscillator initialization etc, a 2 ms delay is generated by the internal state-machine. If the chip temperature rises too high, the Thermal Shutdown (TSD) disables the chip operation and STARTUP mode is entered until no thermal shutdown event is present.
- **BOOST STARTUP:** Soft start for boost output is generated in the BOOST STARTUP mode. The boost output is raised in low current PWM mode during the 4 ms delay generated by the state-machine. All LED outputs are off during the 4 ms delay to ensure smooth startup. The Boost startup is entered from Internal Startup Sequence if EN\_BOOST is HIGH.
- **NORMAL:** During NORMAL mode the user controls the chip using the external PWM input or with Control Registers through I<sup>2</sup>C. The registers can be written in any sequence and any number of bits can be altered in a register in one write.



#### **Functional Overview**

LP8551 is a high voltage LED driver for medium sized LCD backlight applications. It includes high voltage boost converter. Boost voltage automatically sets to the correct level needed to drive the LED strings. This is done by monitoring LED output voltage drop in real time.

Four constant current sinks with PWM control are used for driving LEDs. Constant current value is set with EEPROM bits and with  $R_{\rm ISET}$  resistor. Brightness (PWM) is controlled either with  $I^2C$  register or with PWM input. PWM frequencies are set with EEPROM bits and with  $R_{\rm FSET}$  resistor. Special Phase-Shift PWM mode can be used to reduce boost output current peak, thus reducing output ripple, capacitor size and audible noise.

Safety features include LED fault detection with open and short detection. LED fault detection will prevent system overheating in case of open in some of the LED strings. Chip internal temperature is constantly monitored and based on this LP8551 can reduce the brightness of the backlight to reduce thermal loading once certain trip point is reached. Threshold is programmable in EEPROM. If chip internal temperature reaches too high, the boost converter and LED outputs are completely turned off until the internal temperature has reached acceptable level. Boost converter is protected against too high load current and over-voltage. LP8551 notifies the system about the fault through I<sup>2</sup>C register and with FAULT pin.

#### EEPROM programmable functions include:

- PWM frequencies
- Phase shift PWM mode
- LED constant current
- Boost output frequency
- · Temperature thresholds
- Slope for brightness changes
- PWM output resolution
- · Boost control bits

External components  $R_{\text{ISET}}$  and  $R_{\text{FSET}}$  can also be used for selecting the output current and PWM frequencies.

#### **Block Diagram** $V_{BATT}$ VIN $V_{LDO}$ SW FB TEMP osc Ī SENSOR GND\_SW TSD OUT PLL OUT2 OUT3 V<sub>DDIO</sub> OUT4 PWM >WM LED DETECTOR DRIVERS ISET W-I• LOGIC SCLK I<sup>2</sup>C/ R<sub>FSET</sub> SDA FSET MCU INTERFACE ₩₩ GND\_LED FAULT ΕN EEPROM GNDs

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#### **Clock Generation**

LP8551 has internal 5 MHz oscillator which is used for clocking the boost converter, state machine, PWM outputs, PWM input duty cycle measurement, internal timings such as slope time for output brightness changes.

For PWM output generation the 5 MHz clock can be multiplied with the internal PLL to achieve higher resolution. The higher the clock frequency for PWM generation block, the higher the resolution but the tradeoff is higher  $I_Q$  of the part. Clock multiplication is set with <PWM RESOLUTION[1:0]> EEPROM Bits.

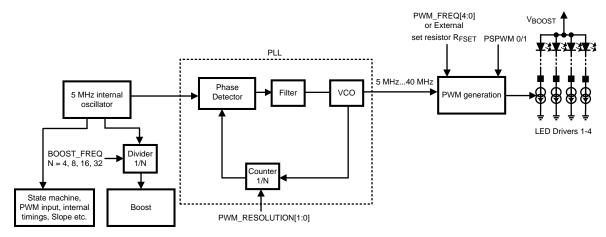


Figure 12. Principle of the Clock Generation

## **Brightness Control Methods**

LP8551 controls the brightness of the backlight with PWM. PWM control is received either from PWM input pin or from I<sup>2</sup>C register bits. The PWM source selection is done with <BRT\_MODE[1:0]> bits as follows:

BRT_MODE[1]	BRT_MODE[0]	PWM source
0	0	PWM input pin duty cycle control. Default.
0	1	PWM input pin duty cycle control.
1	0	Brightness register
1	1	PWM direct control (PWM in = PWM out)

## **PWM Input Duty Cycle**

With PWM input pin duty cycle control the output PWM is controlled by PWM input duty cycle. PWM detector block measures the duty cycle in the PWM pin and uses this 13-bit value to generate the output PWM. Output PWM can have different frequency than input in this mode and also phase shift PWM mode can be used. Slope is effective in this mode. PWM input resolution is defined by the input PWM clock frequency.

#### **Brightness Register Control**

With brightness register control the output PWM is controlled with 8-bit resolution <BRT7:0> register bits. Phase shift scheme can be used with this and the output PWM frequency can be freely selected. Slope is effective in this mode.



#### **PWM Direct Control**

With PWM direct control the output PWM will directly follow the input PWM. Due to the internal logic structure the input is anyway clocked with the 5 MHz clock or the PLL clock. PSPWM mode is not possible in this mode. Slope is not effective in this mode.

#### **PWM Calculation Data Flow**

Below is flow chart of the PWM calculation data flow. In PWM direct control mode most of the blocks are bypassed and this flow chart does not apply.

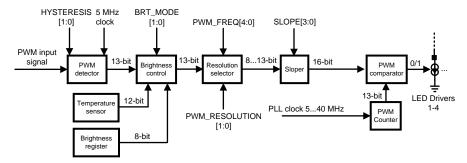


Figure 13. PWM Calculation Data Flow

#### **PWM Detector**

PWM detector block measures the duty cycle of the input PWM signal. Resolution depends on the input signal frequency. Hysteresis selection sets the minimum allowable change to the input. If smaller change is detected, it is ignored. With hysteresis the constant changing between two brightness values is avoided if there is small jitter in the input signal.

## **Brightness Control**

Brightness control block gets 13-bit value from the PWM detector, 12-bit value from the temperature sensor and also 8-bit value from the brightness register. <BRT\_MODE[1:0]> selects whether to use PWM input duty cycle value or the brightness register value as described earlier. Based on the temperature sensor value the duty cycle is reduced if the temperature has reached the temperature limit set to the <TEMP\_LIM[1:0]> EEPROM bits.

## **Resolution Selector**

Resolution selector takes the necessary MSB bits from the input data to match the output resolution. For example if 11-bit resolution is used for output, then 11 MSB bits are selected from the input.

#### Sloper

Sloper makes the smooth transition from one brightness value to another. Slope time can be adjusted from 0 to 500 ms with <SLOPE[3:0]> EEPROM bits. The sloper output is 16-bit value.

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## **PWM Comparator**

The PWM counter clocks the PWM comparator based on the duty cycle value. Output of the PWM comparator controls directly the LED drivers. If PSPWM mode is used, then the signal to each LED output is delayed certain amount.

## **Current Setting**

Maximum current of the LED outputs is controlled with CURRENT[7:0] EEPROM register bits linearly from 0 to 30 mA. If  $\langle EN_I_RES \rangle = 1$  the maximum LED output current can be scaled also with external resistor,  $R_{ISET}$  controls the LED current as follows:

$$I_{LED} = \frac{600 * 1.23V}{R_{ISET}} * \frac{CURRENT [7:0]}{255}$$

Default value for CURRENT[7:0] = 7Fh (127d). Therefore the output current can be calculated as follows:

$$R_{ISET} = \frac{600 * 1.23}{I_{LED}} * \frac{1}{2} = \frac{369}{I_{LED}}$$

E.g. If 16 k $\Omega$  R<sub>ISET</sub> resistor is used, then the LED maximum current is 23 mA.

## **NOTE**

Formula is only approximation for the actual current.



## **PWM Frequency Setting**

PWM frequency is selected with PWM\_FREQ[4:0] EEPROM register. If PLL clock frequency multiplication is used, it will affect the output PWM frequency as well. <PWM\_RESOLUTION[1:0]> EEPROM bits will select the PLL output frequency and hence the PWM frequency and resolution. PWM resolution setting affects the PLL clock frequency (5 MHz...40 MHz). Highlighted frequencies with boldface can be selected also with external resistor  $R_{\text{FSET}}$ . To activate  $R_{\text{FSET}}$  frequency selection the <EN\_F\_RES> EEPROM bit must be 1.

PWM_RES[1:0]	00	01	10	11	
PWM_FREQ[4:0]	5 MHz	10 MHz	20 MHz	40 MHz	Resolution (bits)
11111	19232	-	-	-	8
11110	16828	-	-	-	8
11101	14424	-	-	-	8
11100	12020	-	-	-	8
11011	9616	19232	-	-	9
11010	7963	15927	-	-	9
11001	6386	12771	-	-	9
11000	4808	9616	19232	-	10
10111	4658	9316	18631	-	10
10110	4508	9015	18030	-	10
10101	4357	8715	17429	-	10
10100	4207	8414	16828	-	10
10011	4057	8114	16227	-	10
10010	3907	7813	15626	-	10
10001	3756	7513	15025	-	10
10000	3606	7212	14424	-	10
01111	3456	6912	13823	-	10
01110	3306	6611	13222	-	10
01101	3155	6311	12621	-	10
01100	3005	6010	12020	-	10
01011	2855	5710	11419	-	10
01010	2705	5409	10818	-	10
01001	2554	5109	10217	-	10
01000	2404	4808	9616	19232	11
00111	2179	4357	8715	17429	11
00110	1953	3907	7813	15626	11
00101	1728	3456	6912	13823	11
00100	1503	3005	6010	12020	11
00011	1202	2404	4808	9616	12
00010	1052	2104	4207	8414	12
00001	826	1653	3306	6611	12
00000	601	1202	2404	4808	13

Product Folder Links: LP8551



R<sub>ESET</sub> resistance values with corresponding PWM frequencies:

PWM_RES[1:0]		00	(	01		10	•	11
RFSET (kΩ)	5 MHz Clock	Resolution	10 MHz Clock	Resolution	20 MHz Clock	Resolution	40 MHz Clock	Resolution
1015	19232	8	19232	9	19232	10	19232	11
2629	16828	8	15927	9	16227	10	17429	11
3641	14424	8	12771	9	14424	10	15626	11
5060	12020	8	9616	10	12020	10	12020	11
85100	9616	9	8715	10	9616	11	9616	12
135150	7963	9	7813	10	7813	11	8414	12
200300	6386	9	6311	10	6010	11	6811	12
450	4808	10	4808	11	4808	12	4808	13

#### **Phase Shift PWM Scheme**

Phase shift PWM scheme allows delaying the time when each LED output is active. When the LED output are not activated simultaneously, the peak load current from the boost output is greatly decreased. This reduces the ripple seen on the boost output and allows smaller output capacitors. Reduced ripple also reduces the output ceramic capacitor audible ringing. PSPWM scheme also increases the load frequency seen on boost output by x4 and therefore transfers the possible audible noise to so high frequency that human ear cannot hear it.

Description of the PSPWM mode is seen on the following diagram. PSPWM mode is enabled by setting  $\langle EN_PSPWM \rangle$  EEPROM bit to 1. Shift time is the delay between outputs and it is defined as 1 / ( $f_{PWM} \times 4$ ). If the  $\langle EN_PSPWM \rangle$  bit is 0, then the delay is 0 and all outputs are active simultaneously.

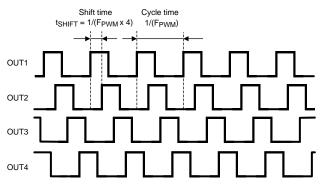


Figure 14. Phase Shift PWM Mode

#### **SLOPE**

Slope time can be programmed with EEPROM bits <SLOPE[3:0]> from 0 to 500 ms. Same slope time is used for sloping up and down. Advanced slope makes brightness changes smooth for eye.



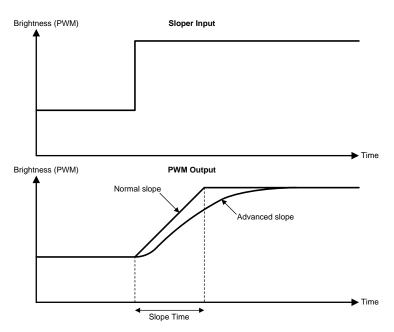


Figure 15. Sloper Operation

#### **Driver Headroom Control**

Driver headroom can be controlled with  $\langle DRV\_HEADR[2:0] \rangle$  EEPROM bits. Driver headroom control sets the minimum threshold for the voltage over the LED output which has the smallest driver headroom and controls the boost output voltage accordingly. Boost output voltage step size is 125 mV. The LED output which has the smallest forward voltage is the one which has highest  $V_F$  across the LEDs. The strings with highest forward voltage is detected automatically. To achieve best possible efficiency smallest possible headroom voltage should be selected. If there is high variation between LED strings, the headroom can be raised slightly to prevent any visual artifacts.

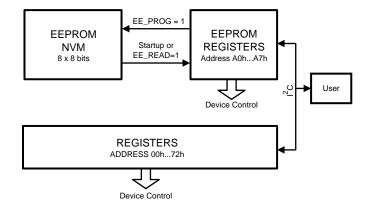
## **EEPROM**

EEPROM memory stores various parameters for chip control. The 64-bit EEPROM memory is organized as 8 x 8 bits. The EEPROM structure consists of a register front-end and the non-volatile memory (NVM). Register data can be read and written through the serial interface, and data will be effective immediately. To read and program NVM, separate commands need to be sent. Erase and program voltages are generated on-chip charge pump, no other voltages than normal input voltage are required. A complete EEPROM memory map is shown in the chapter LP8551 EEPROM Memory Map.

## NOTE

EEPROM NVM can be programmed or read by customer for bench validation. Programming for production devices should be done in TI production test, where appropriate checks will be performed to confirm EEPROM validity. Writing to EEPROM Control register of production devices is not recommended. If special EEPROM configuration is required, please contact the TI Sales Office for availability.



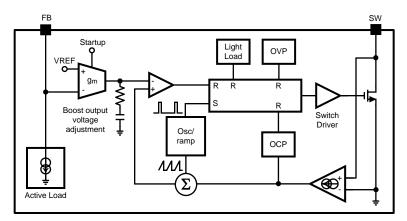


## **Boost Converter**

## Operation

The LP8551 boost DC/DC converter generates a 10...40V supply voltage for the LEDs from 2.7...22V input voltage. The output voltage can be controlled either with EEPROM register bits <VBOOST[4:0]> or automatic adaptive voltage control can be used. The converter is a magnetic switching PWM mode DC/DC converter with a current limit. The topology of the magnetic boost converter is called CPM (current programmed mode) control, where the inductor current is measured and controlled with the feedback. Switching frequency is selectable between 156 kHz and 1.25 MHz with EEPROM bit <BOOST\_FREQ[1:0]>. When <EN\_BOOST> EEPROM register bit is set to 1, then boost will activate automatically when backlight is enabled.

In adaptive mode the boost output voltage is adjusted automatically based on LED driver headroom voltage. Boost output voltage control step size is in this case 125 mV to ensure as small as possible driver headroom and high efficiency. Enabling the adaptive mode is done with <EN\_ADAPT> EEPROM bit. If boost is started with adaptive mode enabled, then the initial boost output voltage value is defined with the <VBOOST[4:0]> EEPROM register bits in order to eliminate long output voltage iteration time when boost is started for the first time. The following figure shows the boost topology with the protection circuitry:



#### **Protection**

Three different protection schemes are implemented:

- 1. Over-voltage protection, limits the maximum output voltage.
  - Over-voltage protection limit changes dynamically based on output voltage setting.
  - Keeps the output below breakdown voltage.
  - Prevents boost operation if battery voltage is much higher than desired output.
- 2. Over-current protection, limits the maximum inductor current.
- 3. Duty cycle limiting.



## **Manual Output Voltage Control**

User can control the boost output voltage with <VBOOST[4:0]> EEPROM register bits when adaptive mode is disabled.

VBOOST	[4:0]	Voltage (typical)
Bin	Dec	Volts
00000	0	10
00001	1	11
00010	2	12
00011	3	13
00100	4	14
11101	29	39
11110	30	40
11111	31	40

## **Adaptive Boost Control**

Adaptive boost control function adjusts the boost output voltage to the minimum sufficient voltage for proper LED driver operation. The output with highest  $V_F$  LED string is detected and boost output voltage adjusted accordingly. Driver headroom can be adjusted with <DRIVER\_HEADR[2:0]> EEPROM bits from ~300 mV to 1200 mV. Boost adaptive control voltage step size is 125 mV. Boost adaptive control operates similarly with and without PSPWM.

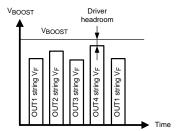


Figure 16. Boost Adaptive Control Principle with PSPWM

## **Fault Detection**

LP8551 has fault detection for LED fault, low-battery voltage, over-current and thermal shutdown. The open drain output pin (FAULT) can be used to indicate occurred fault. The cause for the fault can be read from status register. Reading the fault register will also reset the fault. Setting the EN pin low will also reset the faults, even if an external 5V line is used to power VLDO pin.

#### **LED Fault Detection**

With LED fault detection, the voltages across the LED drivers are constantly monitored. LED fault detection is enabled with <EN\_LED\_FAULT> EEPROM bit. Shorted or open LED string is detected.

If LED fault is detected:

- The corresponding LED string is taken out of boost adaptive control loop;
- Fault bits are set in the fault register to identify whether the fault has been open/short and how many strings are faulty; and
- Fault open-drain pin is pulled down.

LED fault sensitivity can be adjusted with <LED\_FAULT\_THR> EEPROM bit which sets the allowable variation between LED output voltage to 3.3V or 5.3V. Depending on application and how much variation there can be in normal operation between LED string forward voltages this setting can be adjusted.

Fault is cleared by setting EN pin low or by reading the fault register.



## **Under-Voltage Detection**

LP8551 has detection for too-low VIN voltage. Threshold level for the voltage is set with EEPROM register bits as seen in the following table:

UVLO[1:0]	Threshold (V)
00	OFF
01	2.7V
10	5.4V
11	8.1V

When under voltage is detected the LED outputs and boost will shutdown, FAULT pin is pulled down and corresponding fault bit is set in fault register. LEDs and boost will start again when the voltage has increased above the threshold level. Hysteresis is implemented to threshold level to avoid continuous triggering of fault when threshold is reached.

Fault is cleared by setting EN pin low or by reading the fault register.

#### **Over-Current Protection**

LP8551 has detection for too-high loading on the boost converter. When over-current fault is detected, the LP8551 will shut down.

Fault is cleared by setting EN pin low or by reading the fault register.

## **Device Thermal Regulation**

LP8551 has an internal temperature sensor which can be used to measure the junction temperature of the device and protect the device from overheating. During thermal regulation, LED PWM is reduced by 2% of full scale per °C whenever the temperature threshold is reached. Temperature regulation is enabled automatically when chip is enabled. 11-bit temperature value can be read from Temp MSB and Temp LSB registers, MSB should be read first. Temperature limit can be programmed in EEPROM as shown in the following table.

Thermal regulation function does not generate fault signal.

TEMP_LIM[1:0]	Over-Temp Limit (°C)
00	OFF
01	110
10	120
11	130

#### **Thermal Shutdown**

If the LP8551 reaches thermal shutdown temperature (150°C) the LED outputs and boost will shut down to protect it from damage. Also the fault pin will be pulled down to indicate the fault state. Device will activate again when temperature drops below 130°C degrees.

Fault is cleared by setting EN pin low or by reading the fault register.



## I<sup>2</sup>C-Compatible Serial Bus Interface

#### Interface Bus Overview

The I<sup>2</sup>C-compatible synchronous serial interface provides access to the programmable functions and registers on the device. This protocol uses a two-wire interface for bidirectional communications between the IC's connected to the bus. The two interface lines are the Serial Data Line (SDA) and the Serial Clock Line (SCLK). These lines should be connected to a positive supply, via a pull-up resistor and remain HIGH even when the bus is idle.

Every device on the bus is assigned a unique address and acts as either a Master or a Slave depending on whether it generates or receives the SCLK. The LP8551 is always a slave device.

#### **Data Transactions**

One data bit is transferred during each clock pulse. Data is sampled during the high state of the serial clock SCLK. Consequently, throughout the clock's high period, the data should remain stable. Any changes on the SDA line during the high state of the SCLK and in the middle of a transaction, aborts the current transaction. New data should be sent during the low SCLK state. This protocol permits a single data line to transfer both command/control information and data using the synchronous serial clock.

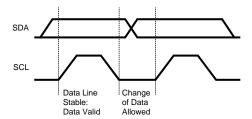


Figure 17. Bit Transfer

Each data transaction is composed of a Start Condition, a number of byte transfers (set by the software) and a Stop Condition to terminate the transaction. Every byte written to the SDA bus must be 8 bits long and is transferred with the most significant bit first. After each byte, an Acknowledge signal must follow. The following sections provide further details of this process.

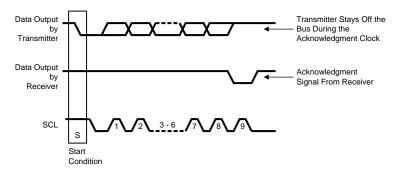


Figure 18. Start and Stop

The Master device on the bus always generates the Start and Stop Conditions (control codes). After a Start Condition is generated, the bus is considered busy and it retains this status until a certain time after a Stop Condition is generated. A high-to-low transition of the data line (SDA) while the clock (SCLK) is high indicates a Start Condition. A low-to-high transition of the SDA line while the SCLK is high indicates a Stop Condition.



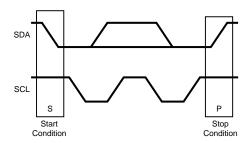


Figure 19. Start and Stop Conditions

In addition to the first Start Condition, a repeated Start Condition can be generated in the middle of a transaction. This allows another device to be accessed, or a register read cycle.

## **Acknowledge Cycle**

The Acknowledge Cycle consists of two signals: the acknowledge clock pulse the master sends with each byte transferred, and the acknowledge signal sent by the receiving device.

The master generates the acknowledge clock pulse on the ninth clock pulse of the byte transfer. The transmitter releases the SDA line (permits it to go high) to allow the receiver to send the acknowledge signal. The receiver must pull down the SDA line during the acknowledge clock pulse and ensure that SDA remains low during the high period of the clock pulse, thus signaling the correct reception of the last data byte and its readiness to receive the next byte.

#### "Acknowledge After Every Byte" Rule

The master generates an acknowledge clock pulse after each byte transfer. The receiver sends an acknowledge signal after every byte received.

There is one exception to the "acknowledge after every byte" rule. When the master is the receiver, it must indicate to the transmitter an end of data by not-acknowledging ("negative acknowledge") the last byte clocked out of the slave. This "negative acknowledge" still includes the acknowledge clock pulse (generated by the master), but the SDA line is not pulled down.

## **Addressing Transfer Formats**

Each device on the bus has a unique slave address. The LP8551 operates as a slave device with 7-bit address combined with data direction bit. Slave address is 2Ch as 7-bit or 58h for write and 59h for read in 8-bit format.

Before any data is transmitted, the master transmits the address of the slave being addressed. The slave device should send an acknowledge signal on the SDA line, once it recognizes its address.

The slave address is the first seven bits after a Start Condition. The direction of the data transfer (R/W) depends on the bit sent after the slave address — the eighth bit.

When the slave address is sent, each device in the system compares this slave address with its own. If there is a match, the device considers itself addressed and sends an acknowledge signal. Depending upon the state of the R/W bit (1:read, 0:write), the device acts as a transmitter or a receiver.

Figure 20. I<sup>2</sup>C Chip Address



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## **Control Register Write Cycle**

- Master device generates start condition.
- Master device sends slave address (7 bits) and the data direction bit (r/w = 0).
- Slave device sends acknowledge signal if the slave address is correct.
- Master sends control register address (8 bits).
- Slave sends acknowledge signal.
- · Master sends data byte to be written to the addressed register.
- Slave sends acknowledge signal.
- If master will send further data bytes the control register address will be incremented by one after acknowledge signal.
- · Write cycle ends when the master creates stop condition.

## **Control Register Read Cycle**

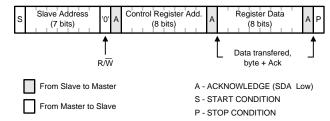
- · Master device generates a start condition.
- Master device sends slave address (7 bits) and the data direction bit (r/w = 0).
- Slave device sends acknowledge signal if the slave address is correct.
- Master sends control register address (8 bits).
- · Slave sends acknowledge signal.
- Master device generates repeated start condition.
- Master sends the slave address (7 bits) and the data direction bit (r/w = 1).
- Slave sends acknowledge signal if the slave address is correct.
- · Slave sends data byte from addressed register.
- If the master device sends acknowledge signal, the control register address will be incremented by one. Slave device sends data byte from addressed register.
- Read cycle ends when the master does not generate acknowledge signal after data byte and generates stop condition.

Table 1. Data Read and Write Cycles

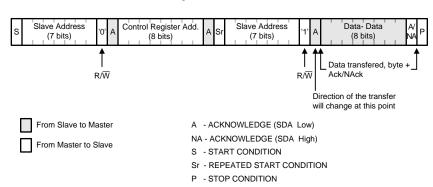
	Address Mode
Data Read	<start condition=""> <slave address=""><r w="0">[Ack] <register addr.="">[Ack] <repeated condition="" start=""> <slave address=""><r w="1">[Ack] [Register Data]<ack nack="" or=""> additional reads from subsequent register address possible <stop condition=""></stop></ack></r></slave></repeated></register></r></slave></start>
Data Write	<start condition=""> <slave address=""><r w="0">[Ack] <register addr.="">[Ack] <register data="">[Ack] additional writes to subsequent register address possible <stop condition=""></stop></register></register></r></slave></start>



## Register Read and Write Detail



#### Register Write Format



Register Read Format



#### **APPLICATIONS INFORMATION**

## **Recommended External Components**

#### **Inductor Selection**

There are two main considerations when choosing an inductor; the inductor should not saturate, and the inductor current ripple should be small enough to achieve the desired output voltage ripple. Different saturation current rating specifications are followed by different manufacturers so attention must be given to details. Saturation current ratings are typically specified at 25°C. However, ratings at the maximum ambient temperature of application should be requested from the manufacturer. Shielded inductors radiate less noise and should be preferred.

The saturation current should be greater than the sum of the maximum load current and the worst case average to peak inductor current.

The equation below shows the worst case conditions.

$$I_{SAT} > \frac{I_{OUTMAX}}{D'} + I_{RIPPLE}$$
Where  $I_{RIPPLE} = \frac{(V_{OUT} - V_{IN})}{(2 \times L \times f)} \times \frac{V_{IN}}{V_{OUT}}$ 

- Where D =  $\frac{(V_{OUT} V_{IN})}{(V_{OUT})}$  and D' = (1 D)
  - I<sub>RIPPLE</sub>: Average to peak inductor current
  - I<sub>OUTMAX</sub>: Maximum load current
  - V<sub>IN</sub>: Maximum input voltage in application
  - L: Min inductor value including worst case tolerances
  - f: Minimum switching frequency
  - D: Duty cycle for CCM Operation
  - V<sub>OUT</sub>: Output voltage

## Example using above equations:

- V<sub>IN</sub> = 12V
- V<sub>OUT</sub> = 38V
- I<sub>OUT</sub> = 400 mA
- $L = 15 \mu H 20\% = 12 \mu H$
- f = 1.25 MHz
- I<sub>SAT</sub> = 1.6A

As a result the inductor should be selected according to the  $I_{SAT}$ . A more conservative and recommended approach is to choose an inductor that has a saturation current rating greater than the maximum current limit of 2.5A. A 15  $\mu$ H inductor with a saturation current rating of 2.5A is recommended for most applications. The inductor's resistance should be less than 300 m $\Omega$  for good efficiency. For high efficiency choose an inductor with high frequency core material such as ferrite to reduce core losses. To minimize radiated noise, use shielded core inductor. Inductor should be placed as close to the SW pin and the IC as possible. Special care should be used when designing the PCB layout to minimize radiated noise and to get good performance from the boost converter. For more information on the PCB layout recommendations, please refer to LP8551TL PCB Layout Guide.

## **Output Capacitor**

A ceramic capacitor with 50V voltage rating or higher is recommended for the output capacitor. The DC-bias effect can reduce the effective capacitance by up to 80%, which needs to be considered in capacitance value selection. For light loads a 4.7  $\mu$ F capacitor is sufficient. Effectively the capacitance should be 4  $\mu$ F for < 150 mA loads. For maximum output voltage/current 10  $\mu$ F capacitor (or two 4.7  $\mu$ F capacitors) is recommended to minimize the output ripple.



## LDO Capacitor

A 1 µF ceramic capacitor with 10V voltage rating is recommended for the LDO capacitor.

## **Output Diode**

A Schottky diode should be used for the output diode. Peak repetitive current should be greater than inductor peak current (2.5A) to ensure reliable operation. Average current rating should be greater than the maximum output current. Schottky diodes with a low forward drop and fast switching speeds are ideal for increasing efficiency in portable applications. Choose a reverse breakdown voltage of the Schottky diode significantly larger (~60V) than the output voltage. Do not use ordinary rectifier diodes, since slow switching speeds and long recovery times cause the efficiency and the load regulation to suffer.

See EEPROM register description on how to select values for these resistors.

## **Register Map**

ADD R	REGISTER	D7	D6	D5	D4	D3	D2	D1	D0	DEFAU LT
00H	Brightness Control		BRT[7:0]							
01H	Device Control						BRT_M	ODE[1:0]	BL_CTL	0000 0000
02H	Fault	OPEN	SHORT	2_CHANN ELS	1_CHANN EL	BL_FAULT	OCP	TSD	UVLO	0000 0000
03H	ID	PANEL		MF	G[3:0]	•		REV[2:0]	•	1111 1100
04H	Direct Control						TUO	[4:1]		0000 0000
05H	Temp MSB				TEM	IP[10:3]				0000 0000
06H	Temp LSB		TEMP[2:0]						0000 0000	
72H	EEPROM_cont rol	EE_READ Y					EE_INIT	EE_PROG	EE_READ	0000 0000

## **EEPROM Memory Map**

ADD R	REGIS TER	D7	D6	D5	D4	D3	D2	D1	D0		
A0H	eeprom addr 0			CURRENT[7:0]							
A1H	eeprom addr 1	BOOST_FREQ[1:0] EN_LED_FAU TEMP_LIM[1:0] SLOPE[2:0]				SLOPE[2:0]					
A2H	eeprom addr 2	ADAPTIVE_S	SPEED[1:0]	ADV_SLOPE		EN_ADAPT	EN_BOOST BOOST_IM AX				
АЗН	eeprom addr 3	UVLO	P[1:0]	EN_PS	SPWM		PWM_FREQ[4:0]				
A4H	eeprom addr 4	PWM_RESOI	LUTION[1:0]	EN_I_RES	LED_FAULT _THR		DF	RV_HEADR[2:0	)]		
A5H	eeprom addr 5					,	VBOOST[4:0]				
A6H	eeprom addr 6										
А7Н	eeprom addr 7						EN_F_RES	HYSTER	ESIS[1:0]		

Product Folder Links: *LP8551* 

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# **Register Bit Explanations**

# **Brightness Control**

Address 00h

Reset value 0000 0000b

Brightness Cont	Brightness Control register															
7 6 5 4 3 2 1 0																
	BRT[7:0]															
Name	Bit	Access	Description													
BRT	7:0	R/W	Backlight PWM	8-bit linear contro	ol.		BRT 7:0 R/W Backlight PWM 8-bit linear control.									

## **Device Control**

Address 01h

Reset value 0000 0000b

7	6	5	4	3	2	1	0	
					BRT_M	1ODE[1:0]	BL_CTL	
Name	Bit	Access	Description					
BRT_MODE	2:1	R/W	PWM source m	ode				
			00b = PWM inp	out pin duty cycle o	control (default)			
			01b = PWM input pin duty cycle control					
			10b = Brightnes	ss register				
			11b = Direct P\	NM control from P	WM input pin			
BL_CTL	0	R/W	Enable backligh	nt				
				isabled and chip to state of the chip is				
				nabled and chip to state of the chip is				



## Fault

Address 02h

Reset value 0000 0000b

Fault register		T		T.	1	I			
7	6	5	4	3	2	1	0		
OPEN	SHORT	2_CHANNELS	1_CHANNEL	BL_FAULT	OCP	TSD	UVLO		
Name	Bit	Access	Description						
OPEN	7	R	LED open fault detec	tion					
			0 = No fault						
			1 = LED open fault do the register 02h or se		pulled to GND.	Fault is cleared	d by reading		
SHORT	6	R	LED short fault detec	tion					
			0 = No fault						
			1 = LED short fault do the register 02h or se		pulled to GND.	Fault is cleared	d by reading		
2_CHANNELS	5	R	LED fault detection						
			0 = No fault						
			1 = 2 or more channel GND. Fault is cleared						
1_CHANNEL	4	R	LED fault detection						
			0 = No fault						
			1 = 1 channel has ge Fault is cleared by re				d to GND.		
BL_FAULT	3	R	LED fault detection						
			0 = No fault						
			1 = LED fault detecte pulled to GND. Fault						
OCP	2	R	Over current protection	on					
			0 = No fault						
			1 = Over current dete output and if the boos OCP fault and disable reading the register 0 again.	st output has been to the boost. Fault pi	oo low for more n is pulled to GN	than 50 ms it v ND. Fault is cle	vill generate ared by		
TSD	1	R	Thermal shutdown						
			0 = No fault						
			1 = Thermal fault generated, 150 °C reached. Boost converted and be disabled until the temperature has dropped down to 130 °C. Fault GND. Fault is cleared by reading the register 02h or setting EN pin						
UVLO	0	R	Under voltage detecti	on					
			0 = No fault						
			1 = Under voltage de disabled until V <sub>IN</sub> volt EEPROM bits from 3 register 02h or setting	age is above the thi V9V. Fault pin is p	reshold voltage.	Threshold volta	age is set with		

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## Identification

Address 03h

Reset value 1111 1100b

Identification	dentification register											
7	6	5	4	3	2	1	0					
PANEL		М	MFG[3:0] REV[2:0]									
Name	Bit	Access	Description									
PANEL	7	R	Panel ID code									
MFG	6:3	R	Manufacturer ID o	code								
REV	2:0	R	Revision ID code									

# **Direct Control**

Address 04h

Reset value 0000 0000b

Direct Control	register									
7	6	5	4	4 3 2 1						
					OUT[	4:1]				
Name	Bit	Access	Description							
OUT	3:0	R/W	Direct control of	the LED outputs						
			0 = Normal ope	ration. LED output a	re controlled with P	WM.				
			1 = LED output is forced to 100% PWM.							

# **Temp MSB**

Address 05h

Reset value 0000 0000b

Temp MSB re	gister								
7	6	5	4	3	2	1	0		
			TE	MP[10:3]					
Name	Bit	Access	Description						
TEMP	7:0	R	Device internal temperature sensor reading first 8 MSB. MSB must be read before LSB, because reading of MSB register latches the data.						

# Temp LSB

Address 06h

Reset value 0000 0000b

Temp LSB re	Temp LSB register											
7	6	5	4	3	2	1	0					
	TEMP[2:0]	•										
Name	Bit	Access	Description	Description								
TEMP	7:5	R	Device internal temperature sensor reading last 3 LSB. MSB must be read before LSB, because reading of MSB register latches the data.									



#### **EEPROM Control**

Address 72h

Reset value 0000 0000b

EEPROM Control r	egister									
7	6	5	4	3	2	1	0			
EE_READY					EE_INIT	EE_PROG	EE_READ			
Name	Bit	Access	Description							
EE_READY	7	R	EEPROM re	ady						
			0 = EEPRO	M programming	or read in progress					
			1 = EEPRO	M ready, not bus	sy					
EE_INIT	2	R/W	EEPROM initialization bit. This bit must be written 1 before EEPROM read or programming.							
EE_PROG	1	R/W	EEPROM programming.							
			0 = Normal operation							
			EEPROM pr	rogramming can non volatile mem	ramming sequence. be started. Program nory (NVM). Prograr generated inside the	ns data currently in t mming sequence tak	he EEPROM			
EE_READ	0	R/W	EEPROM re	ead						
			0 = Normal operation							
			1 = Reads the data from NVM to the EEPROM registers. Can be used to restore default values if EEPROM registers are changed during testing.							

Programming sequence (program data permanently from registers to NVM):

- 1. Turn on the chip by writing BL\_CTL bit to 1 and BRT\_MODE[1:0] to 10b (05h to address 01h)
- 2. Write data to EEPROM registers (address A0h...A7h)
- 3. Write EE\_INIT to 1 in address 72h. (04h to address 72h)
- 4. Write EE PROG to 1 and EE INIT to 0 in address 72h. (02h to address 72h)
- 5. Wait 200 ms.
- 6. Write EE\_PROG to 0 in address 72h. (00h to address 72h)

Read sequence (load data from NVM to registers):

- 1. Turn on the chip by writing BL\_CTL bit to 1 and BRT\_MODE[1:0] to 10b (05h to address 01h).
- 2. Write EE\_INIT to 1 in address 72h. (04h to address 72h)
- 3. Write EE\_READ to 1 and EE\_INIT to 0 in address 72h. (01h to address 72h)
- 4. Wait 200 ms.
- 5. Write EE\_READ to 0 in address 72h. (00h to address 72h)

## **NOTE**

Data written to EEPROM registers is effective immediately even if the EEPROM programming sequence has not been done. When power is turned off, the device will however lose the data if it is not programmed to the NVM. During startup device automatically loads the data from NVM to registers.

#### NOTE

EEPROM NVM can be programmed or read by customer for bench validation. Programming for production devices should be done in TI production test, where appropriate checks will be performed to confirm EEPROM validity. Writing to EEPROM Control register of production devices is not recommended. If special EEPROM configuration is required, please contact the TI Sales Office for availability.

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# **EEPROM Bit Explanations**

# **EEPROM Default Values**

ADDR	Default value				
A0h	0111 1111				
A1h	1011 0101				
A2h	1010 1110				
A3h	0111 1011				
A4h	0010 0000				
A5h	0000 1001				
A6h	0000 0000				
A7h	0000 0101				

# **EEPROM Address 0**

Address A0h

_	_	_		_	_			
7	6	5	4	3	2	1	0	
			CURF	RENT[7:0]				
Name	Bit	Access			Description			
CURRENT	7:0	R/W	defined only wit	th these bits a ted to ISET p	If EN_I_RES = 0 the is described below. If E in also scales the LED tout current is then 23	EN_I_RES = 1, the current. With 16 kg	n the external	
				EN_I_RES = 0		EN_I_F	RES = 1	
			0000	0000	0 mA	0 mA		
			0000	0001	0.12 mA	(1/255) x 600	x 1.23V/R <sub>ISET</sub>	
			0000	0010	0.24 mA	(2/255) x 600	x 1.23V/R <sub>ISET</sub>	
			0111 1111	(default)	15.00 mA	(127/255) x 600	0 x 1.23V/R <sub>ISI</sub>	
			1111	1101	29.76 mA	29.76 mA (253/255) x 600		
			1111	1110	29.88 mA	(254/255) x 600	0 x 1.23V/R <sub>ISI</sub>	
			1111	1111	30.00 mA	(255/255) x 600 x 1.23V/F		

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Address A1h

7	6	5	4	3	2	1	0		
BOOST_FREQ	[1:0]	EN_LED_FAULT	TEMP_L	-IM[1:0]		SLOPE[2:0]			
Name	Bit	Access	Description						
BOOST_FREQ	7:6	R/W	Boost Converte	r Switch Freque	ency				
			00 = 156 kHz						
			01 = 312 kHz						
			10 = 625 kHz						
			11 = 1250 kHz						
EN_LED_FAULT	5	R/W	Enable LED fau	ult detection					
			0 = LED fault detection disabled						
			1 = LED fault detection enabled						
TEMP_LIM 4:	4:3	R/W	Thermal deration function temperature threshold						
			00 = thermal deration function disabled						
			01 = 110 °C						
			10 = 120 °C						
			11 = 130 °C						
SLOPE	2:0	R/W	Slope time for brightness change						
			000 = Slope fur	nction disabled,	immediate brig	htness change			
			001 = 50 ms						
			010 = 75  ms						
			011 = 100 ms						
			100 = 150 ms						
			101 = 200 ms						
			110 = 300 ms						
			111 = 500  ms						



Address A2h

7	6	5	4	3	2	1	0		
ADAPTIVE_SPEE	ED[1:0]	ADV_SLOPE		EN_ADAPT	EN_BOOST	BOOST_IMAX			
Name	Bit	Access	Description						
ADAPTIVE	7	R/W	Boost converter adaptive control speed adjustment						
SPEED[1]			0 = Normal mo	de					
				node optimized for ng boost / backligh		ating this helps the vo	Itage droop wit		
ADAPTIVE	6	R/W	Boost converte	er adaptive control	speed adjustmen	t			
SPEED[0]			0 = Adjust boo	st once for each pl	nase shift cycle o	r normal PWM cycle			
			1 = Adjust boo	st every 16th phas	e shift cycle or no	ormal PWM cycle			
ADV_SLOPE	5	R/W	Advanced slope						
			0 = Advanced slope is disabled						
			1 = Use advanced slope for brightness change to make brightness changes smooth for eye						
EN_ADAPT	3	R/W	Enable boost converter adaptive mode						
			0 = adaptive mode disabled, boost converter output voltage is set with VBOOST EEPROM register bits						
			1 = adaptive mode enabled. Boost converter startup voltage is set with VBOOST EEPROM register bits, and after startup voltage is reached the boost converter will adapt to the highest LED string V <sub>F</sub> . LED driver output headroom is set with DRV HEADR EEPROM control bits.						
EN_BOOST	2	R/W	Enable boost of	converter					
		0 = boost is disabled							
			1 = boost is en	abled and will turn	on automatically	when backlight is en	abled		
BOOST_IMAX	1	R/W	Boost converte	er inductor maximu	m current				
		· · · · ·	0 = 1.4A						
			1 = 2.5A (reco	mmended)					



Address A3h

		1						
7	6	5	4	3	2	1	0	
UVLO[1:	0]	EN_PSPWM		F	WM_FREQ[4:0]			
Name	Bit	Access	Description					
UVLO	7:6	R/W	00 = Disabled					
			01 = 2.7V					
			10 = 5.4V					
			11 = 8.1V					
EN_PSPWM	5	R/W	Enable phase sh	nift PWM schei	me			
			0 = phase shift F	PWM disabled,	normal PWM mo	ode used		
			1 = phase shift F	PWM enabled				
PWM_FREQ	4:0	R/W	PWM output frequency setting. See PWM Frequency Setting for full description of selectable PWM frequencies.					

## **EEPROM Address 4**

Address A4h

EEPROM ADDRESS	4 register									
7	6	5	4	3	2	1	0			
PWM_RESOLUTI	ON[1:0]	EN_I_RES	LED_FAULT_THR			DRV_HEADR[2	:0]			
Name	Bit	Access	Description							
PWM RESOLUTION	7:6	R/W	PWM output resolution selection. Actual resolution depends also on the output frequency. See PWM Frequency Setting for full description.							
			00 = 810 bits (19.2 kHz4.8 kHz)							
			01 = 911 bits (19.2 l	kHz 4.8 kHz)						
			10 = 1012 bits (19.2	kHz4.8 kHz)						
			11 = 1113 bits (19.2	kHz4.8 kHz)						
EN_I_RES	5	R/W	Enable LED current se	et resistor						
			0 = Resistor is disabled and current is set only with CURRENT EEPROM register bits							
		1 = Enable LED current set resistor. LED current is defined by the R <sub>ISET</sub> resist CURRENT EEPROM register bits.								
LED_FAULT_THR	4	R/W	LED fault detector thresholds. $V_{\text{SAT}}$ is the saturation voltage of the driver, typically 200 mV.							
			0 = 3.3V							
			1 = 5.3V							
DRV_HEADR	2:0	R/W	LED output driver hea 200 mV.	droom control. V	SAT is the saturat	ion voltage of the	e driver, typically			
			000 = V <sub>SAT</sub> + 125 mV							
			$001 = V_{SAT} + 250 \text{ mV}$							
			010 = V <sub>SAT</sub> + 375 mV							
			$011 = V_{SAT} + 500 \text{ mV}$							
			100 = V <sub>SAT</sub> + 625 mV							
			101 = V <sub>SAT</sub> + 750 mV							
			110 = V <sub>SAT</sub> + 875 mV							
			111 = V <sub>SAT</sub> + 1000 m <sup>3</sup>	V						

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Address A5h

7	6	5	4	3	2	1	0			
				•	VBOOST[4:0]					
Name	Bit	Access	Description							
VBOOST	4:0	R/W	enabled, this se	Boost voltage control from 10V to 40V with 1V step. If adaptive boost control is enabled, this sets the initial start voltage for the boost converter. If adaptive mod is disabled, this will directly set the output voltage of the boost converter.						
			0 0000 = 10V							
			0 0001 = 11V							
			0 0010 = 12V							
			1 1101 = 39V							
			1 1110 = 40V							
			1 1111 = 40V							

# **EEPROM Address 7**

Address A7h

EEPROM ADDRE	SS 7 registe	er								
7	6	5	4	3	2	1	0			
					EN_F_RES	HYSTER	RESIS[1:0]			
Name	Bit	Access	Description							
EN_F_RES	2	R/W	Enable PWM out	out frequency se	t resistor					
			0 = Resistor is disabled and PWM output frequency is set with PWM_FREQ EEPROM register bits							
			1 = PWM frequency set resistor is enabled. $R_{FSET}$ defines the output PWM frequency. See PWM Frequency Setting for full description of the PWM frequencies.							
HYSTERESIS	1:0	R/W	PWM input hysteresis function. Will define how small changes in the PWM input are ignored to remove constant switching between two values.							
			00 = OFF							
			01 = 1-bit hysteresis with 11-bit resolution							
			10 = 1-bit hysteresis with 10-bit resolution							
			11 = 1-bit hystere							



# **REVISION HISTORY**

CI	nanges from Revision C (April 2013) to Revision D	Page
•	Changed top mark drawing to reflect TI nomenclature	2
•	Added EEPROM note	. 17
•	Added EEPROM note	. 30



# PACKAGE OPTION ADDENDUM

18-Nov-2013

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LP8551TLE/NOPB	ACTIVE	DSBGA	YZR	25	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		8551	Samples
LP8551TLX/NOPB	ACTIVE	DSBGA	YZR	25	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-30 to 85	8551	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

18-Nov-2013

n no event shall TI's liabili	tv arising out of such information	exceed the total purchase	price of the TI part(s)	at issue in this document sold by	TI to Customer on an annual basis.

# PACKAGE MATERIALS INFORMATION

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# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

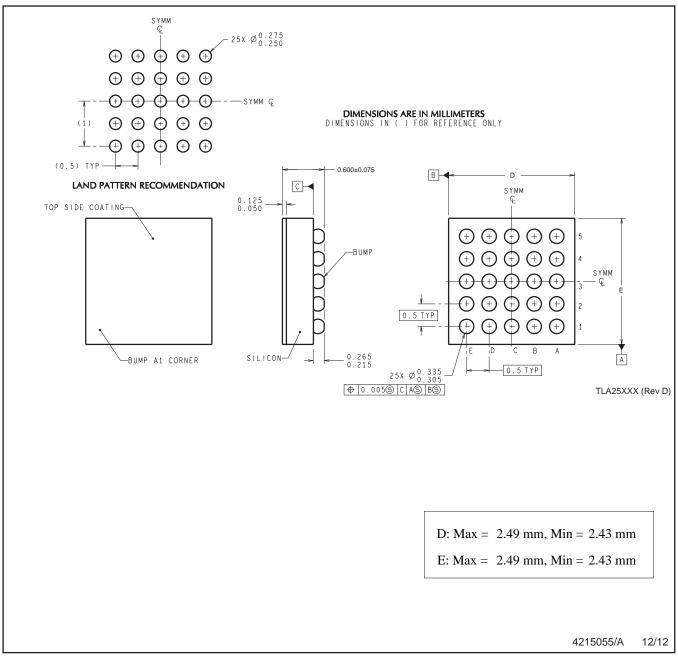
Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LP8551TLE/NOPB	DSBGA	YZR	25	250	178.0	8.4	2.69	2.69	0.76	4.0	8.0	Q1
LP8551TLX/NOPB	DSBGA	YZR	25	3000	178.0	8.4	2.69	2.69	0.76	4.0	8.0	Q1

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\*All dimensions are nominal

Device	Package Type Package D		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LP8551TLE/NOPB	DSBGA	YZR	25	250	210.0	185.0	35.0
LP8551TLX/NOPB	DSBGA	YZR	25	3000	210.0	185.0	35.0



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994. B. This drawing is subject to change without notice.

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